

2N4125



PNP General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring collector currents of 10 μA to 100 mA.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V_{CEO}	Collector-Emitter Voltage	30	V	
V _{CBO}	Collector-Base Voltage	30	V	
V _{EBO}	Emitter-Base Voltage 4.0		V	
lc	Collector Current - Continuous	200	mA	
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C	

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		2N4125	
P _D	Total Device Dissipation	625	mW
	Derate above 25°C	5.0	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

PNP General Purpose Amplifier (continued)

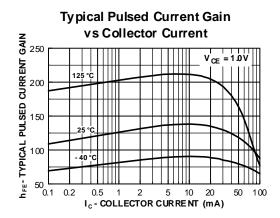
Electr	Electrical Characteristics TA = 25°C unless otherwise noted					
Symbol	Parameter	Test Conditions	Min	Max	Units	
OFF CHA	RACTERISTICS					
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 1.0 \text{ mA}, I_B = 0$	30		V	
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 10 \mu A, I_E = 0$	30		V	
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 10 \mu A, I_C = 0$	4.0		V	
I _{CBO}	Collector-Cutoff Current	$V_{CB} = 20 \text{ V}, I_{E} = 0$		50	nA	
I _{EBO}	Emitter-Cutoff Current	V _{EB} = 3.0 V, I _C = 0		50	nA	
	Collector-Emitter Saturation Voltage	$V_{CE} = 1.0 \text{ V}, I_{C} = 2.0 \text{ mA}$ $V_{CE} = 1.0 \text{ V}, I_{C} = 50 \text{ mA}$ $I_{C} = 50 \text{ mA}, I_{B} = 5.0 \text{ mA}$	25	0.4	V	
h _{FF}	RACTERISTICS* DC Current Gain	$V_{CE} = 1.0 \text{ V}, I_{C} = 2.0 \text{ mA}$	50	150		
V _{CE(sat)}	Collector-Emitter Saturation Voltage			0.4	V	
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$		0.95	V	
C _{ob}	IGNAL CHARACTERISTICS Output Capacitance	V _{CB} = 5.0 V, f = 100 kHz		4.5	pF	
C _{ib}	Input Capacitance	$V_{BE} = 0.5 \text{ V}, f = 100 \text{ kHz}$		10	pF	
h _{fe}	Small-Signal Current Gain	$I_C = 2.0 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 1.0 kHz $I_C = 10 \text{ mA}, V_{CE} = 20 \text{ V},$ f = 100 MHz	50 2.0	200		
NF	Noise Figure	V_{CE} = 5.0 V, I_{C} = 100 μA, R_{S} = 1.0 kΩ, f = 10Hz to 15.7 kHz,		5.0	dB	

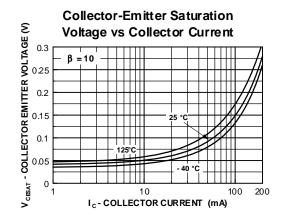
^{*}Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

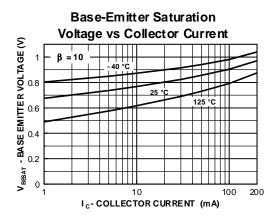
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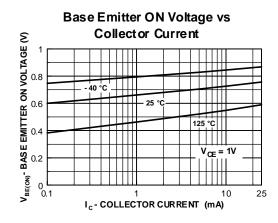
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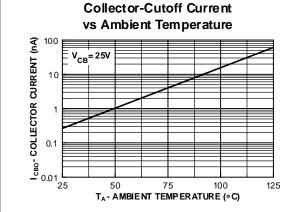
Typical Characteristics

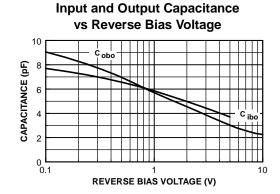










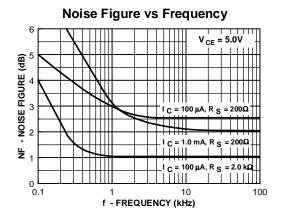


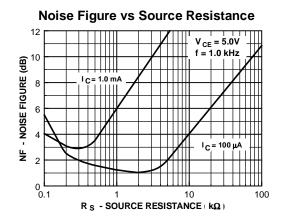
Common-Base Open Circuit

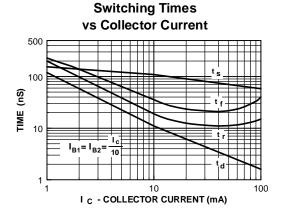
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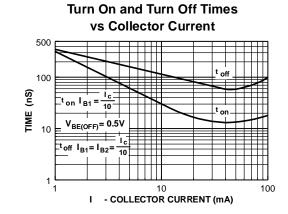
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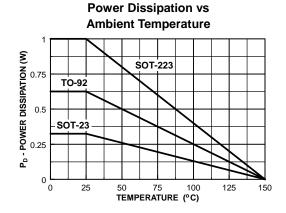
Typical Characteristics (continued)







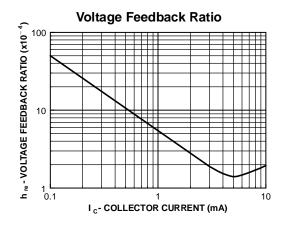


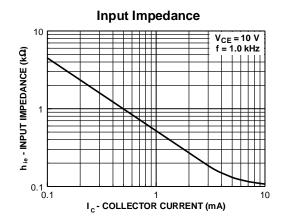


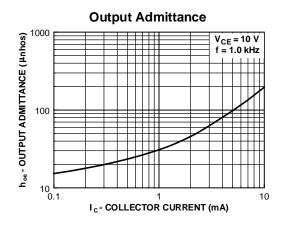
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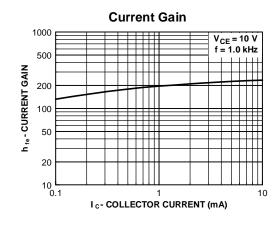
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Typical Characteristics (continued)









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